

**AMENDMENTS TO THE CLAIMS**

Claim 1 (currently amended): A method of forming a photo sensor in a photo diode formed on a semiconductor wafer, a surface of the semiconductor comprising a substrate with first-type dopants, and an insulating layer positioned on ~~a surface~~ the surface of the substrate and surrounding the photo sensor, the method comprising:

10     forming a first mask layer on the surface of the substrate for defining positions of a plurality of first doped regions in the photo sensor;

       performing a first ion implantation process utilizing second-type dopants to form ~~a plurality~~ the plurality of first doped regions on ~~a surface~~ the surface of the photo sensor;

15     removing the first mask layer and forming a second mask layer surrounding the photo sensor; and

       performing a second ion implantation process utilizing second-type dopants to form a second doped region on the surface of the photo sensor, and the second doped region being overlapped with a partial region of each of the first doped regions.

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25     Claim 2 (original): The method of claim 1 wherein the dopants in the first doped regions and in the second doped region interact with neighboring substrate to form a plurality of depletion regions.

30     Claim 3 (original): The method of claim 1 wherein the first-type dopants are N-type, and the second-type dopants are P-type.

Claim 4 (original): The method of claim 1 wherein the first-type dopants are P-type, and the second-type dopants are N-type.

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Claim 5 (original): The method of claim 1 wherein the substrate further comprises an epitaxial silicon layer, and each of the first doped regions and the second doped region are formed inside the epitaxial silicon layer.

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Claim 6 (original): The method of claim 1 wherein a dopant density of the first ion implantation process is less than a dopant density of the second ion implantation process.

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Claim 7 (original): The method of claim 1 wherein the surface of the semiconductor wafer further comprises a logic circuit region, and the second ion implantation process forms at least a lightly doped drain (LDD) within the logic circuit region.

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Claim 8 (original): The method of claim 1 wherein the method further comprises an annealing process for driving-in the dopants in the second doped region.

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Claim 9 (original): The method of claim 1 wherein each of the depletion regions formed between the neighboring first doped regions is a complete depletion region, and a capacitance of each of the depletion regions is approximately equal to zero for increasing a sensing area, decreasing dark current, and further increasing photo current and photon

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conversion gain.

Claim 10 (original): The method of claim 1 wherein the  
second doped region is utilized to be a conducting wire  
5 of the photo sensor.

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